O DE 247	COLL STREET OF THE STREET OF T
क्रांध्य	TF
	(to be use
7	

TRANSMITTAL FORM	Application No.	10/695,724
TRANSIVITI TAL PURIVI	Filing Date	October 28, 2003
(to be used for all correspondence after initial filin	First Named Inventor	Eric Frayssinet
	Art Unit	
	Examiner Name	Rori Burch
Total Number of Pages in This Submission 5	Attorney Docket Number	15675P314CX

ENCLOSURES (check all that apply)							
Fee Transmittal F	form	Drawing(s)	After Allowance Communication to Group				
Fee Attache	ed	Licensing-related Papers	Appeal Communication to Board of Appeals and Interferences				
Amendment / Res	ponse	Petition	Appeal Communication to Group (Appeal Notice, Brief, Reply Brief)				
After Final Affidavits/de	eclaration(s)	Petition to Convert a Provisional Application	Proprietary Information				
Extension of Time	Request	Power of Attorney, Revocation Change of Correspondence Address	Status Letter				
Express Abandonr	ment Request	Terminal Disclaimer	Other Enclosure(s) (please identify below):				
Information Disclo		Request for Refund	Prior Art References (17); return postcard				
Certified Copy of I		CD, Number of CD(s)					
	ation Filing Fee ation/POA to Missing r 37 CFR	Remarks					
	SIGNATUR	E OF APPLICANT, ATTORNEY, OR A	GENT				
Firm or Individual name	Eric S. Hyman, Reg. No. 30,139 BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP						
Signature							
Date // /3 /3 (63							
CERTIFICATE OF MAILING/TRANSMISSION							
I hereby certify that this correspondence is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.							
Typed or printed nar	me Melissa Stea	d ,					
Signature	Me						

DEL 2 4 2003 STEEL

fer FY 2003

Effective 01/01/2003. Patent fees are subject to annual revision.

Applicant claims small entity status. See 37 CFR 1.27.

TOTAL AMOUNT OF PAYMENT

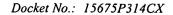
(\$)

Complete if Kn wn					
Application Number	10/695,724				
Filing Date	October 28, 2003				
First Named Inventor	Eric Frayssinet				
Examiner Name	Rori Burch				
Group/Art Unit					
Attorney Docket No.	15675D31ACY				

Date

	METHOD OF PAYMENT (check all that apply)				FEE CALCULATION (continued)									
U	☐ Check ☐ Credit card ☐ Money ☐ Other ☐ None			3. A	DDITIO	NAL	FEES	3						
	☐ Check ☐ Deposit A		it card	Money Order		er LINone	Larg	e Entity	ı Sma	II Entity	y			
Ì	Deposit P	eccorn.					Fee	Fee	Fee	Fee	<u> </u>			
	Deposit Account			02-266	6	1	Code	(\$)	Code	(\$)	Fe	e Description		FeePaid
	Number						1051 1052	130 50	2051 2052	65 25	Surcharge - late filing Surcharge - late provi			
	Deposit Account	Blokel	v Soko	oloff, Taylo	or & 70	fman IID	luz.	3.0	2002	۳	cover sheet.	Sichai ming lee ci		
-	Name	Diakei	y, soke	non, rayı	01 & Z.a.	man LLF	2053	130	2053	130	Non-English specificat			
-				o: (check all the			1812	2,520 920 *	1812	2,520 920	For filing a request for Requesting publication	· ·	nation	
ı	Charge fe	e(s) indicate	d below		Credit any ove	erpayments	1804	320	1804	320	Examiner action	IT OF SITY PRIOR ID		
ı	Charge a	ny additional	fee(s) requ	ired under 37 C	FR §§ 1.16,	1.17, 1.18 and 1.20.	1805	1,840 *	1805	1,840	* Requesting publication	n of SIR after		
ı		ee(s) indicate		except for the fi	ling fee			440		ee.	Extension for reply wi	thin first month		
ŀ				LCULATIO	N	Elyacide Field Tyde, Maced American	1251 1252	110 420	2251	55 210	Extension for reply wit			<u> </u>
ŀ	1. BA	SIC FILI			714	Mile Build of the Confederation (Confederation Confederation Confederati	1253	950	2253	475	Extension for reply will			<u> </u>
ı	Large Entity		II Entity	_			1254	1,480	2254	740	Extension for reply wi			
	Fee Fo	e Fee	Fee [Fee Description	-	FeePaid	1255	1,210	2255	605	Extension for reply wi	thin fifth month		
	,						1404	330	2401	165	Notice of Appeal			<u> </u>
ı		70 2001 40 2002	385 170	Utility filing fee Design filing fe			1402	330	2402	165	Filing a brief in suppo	t of an appeal		
		30 2003	265	Plant filing fee			1403	290	2403	145	Request for oral heari	ng		
ı		70 2004	386	Reissue filing			1451	1,510	2451	1,510	Petition to institute a p	oublic use proceedi	ing	
ŀ	1005 1	60 2005	80	Provisional fili	ng fee		1452	110	2452	55	Petition to revive - una	avoidable		
ı		•	SUBT	TOTAL (1)	(\$)		1453	1,330	2453	665	Petition to revive - uni	ntentional		
ŀ							1501	1,330	2501	665	Utility issue fee (or re	ssue)		I
ŀ	2. EX	TRA CL	AIM FE	ES _{Extra} Claims	Fee from below	FeePaid	1502 1503	480 640	2502 2503	240 320	Design issue fee Plant issue fee			<u> </u>
ŀ	Total Claims]. 20"	_ X		7=[1460	130	2460	130	Petitions to the Comn	nissioner		<u> </u>
ŀ	Independent Claims	-	. 20		+	- ₌	1807	50	1807	50	Processing fee under			
	Multiple Depen	dent				- =	1806	180	1806	180	Submission of Inform	ation Disclosure St	tmt	
2	Large Entity	Small	Entity		L		8021	40	8021	40	Recording each pater	t assignment per		<u> </u>
	Fee Fe Code (\$		Fee (\$)	Fee Description	<u> </u>						property (times numb			
	•		***	Olaina in assau			1809	770	1809	385	Filing a submission aff (37 CFR § 1.129(a))	er final rejection		
The state of the s	1202 1 1201 8		9 43	Claims in excess Independent cla		s of 3	1810	770	2810	385	For each additional in			<u></u>
	1203 29		145	Multiple Depend							examined (37 CFR §			
	1204 8	2204	43	**Reissue indepe	endent claims	over original	1801	770	2801	385	Request for Continued		E)	
	4	,	•	·		100 and aven	1802	900	1802	900	Request for expedited of a design application	examination		
1	1205 1	2205	9	**Reissue claim: original pater		1 20 MIN OVER	Other fo	ee (specify)						
	SUBTOTAL (2) (\$)													
	**or number previously paid, if greater, For Reissues, see below				ee below	* Reduce	ed by Basic F	iling Fee	Paid	:	SUBTOTAL (3)	(\$)		
6	SURMI	ITED B	7		Sale (leaf alloway	and the second s	-ful action()	The second secon				Comr	olete (if applicat	ole)
f	Name (Pr			. II.	-			egistratio		T	20.120			
	IVALLIE (PI	ни гуре)	Eric S	S. Hyman		-,		ttorney/Age		3	30,139	Telephone	(310) 207	-2000

Signature





IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:

ERIC FRAYSSINET, ET AL.

Application No.: 10/695,724

Filed: October 28, 2003

For: METHOD FOR PRODUCING A GALLIUM

NITRIDE EPITAXIAL LAYER

Art Group:

Examiner: Rori Burch

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In accordance with the duty of disclosure, enclosed is a copy of Information Disclosure Statement by Applicant (form PTO/SB/08), which is being submitted within three (3) months of filing of the application. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Date: / 1/18/63

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Eric S. Hyman Reg. No. 30,139

12400 Wilshire Boulevard, 7th Floor Los Angeles, CA 90025 Telephone: (310) 207-3800

I hereby certify that this correspondence is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Melissa Stead

Date

OF E JOB E

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet of

Complete if Known				
Application Number	10/695,724			
Filing Date	October 28, 2003			
First Named Inventor	Eric Frayssinet			
Art Unit				
Examiner Name	Rori Burch			
Attorney Docket Number	15675P314CX			

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
		"Selective area epitaxy of GaN for electron field emission devices", D. Kapolnek, et al., Journal of Crystal Growth 170 (1997) pgs 340-343	
		"Selective growth of wirtzite GaN and A1xGa1-xN on GaN/sapphire substrates by metalorganic vapor phase epitaxy", Y. Kato, et al., Journal of Crystal Grown 144 (1994) 133-140	
		"The effect of the Si/N treatment of a nitridated sapphire surface on the growth mode of GaN in low-pressure metalorganic vapor phase epitaxy", S. Haffouz, et al., 1998 American Institute of Physics, vol. 73, no. 9, august 31, 1998, p 1278-1280	
		"Influence of in sity sapphire surface preparation and carrier gas on the growth mode of GaN in MOVPE", P. Vennegues, et al., Journal of Crystal Growth, pgs 167-177	
		"Effect of Magnesium and Silicon on the lateral overgrowth of GaN patterned substrates by Metal Organic Vapor Phase Epitaxy", S. Haffouz, et al., MRS Internet Journal Nitride Semiconductor Research, pg 1-6	-
		"Growth of high-quality GaN by low-pressure metal-organic vapour phase epitxy (LP-MOVPE) from 3D islands and lateral overgrowth", H. Lahreche, et al., Journal of Crystal Growth, pgs 245-252	
		"Anti-Surfactant in III-Nitride Epitaxy -Quantum Dot Formation and Dislocation Termination-", S. Tanaka, et al, Appl. Vol. 39 (2000) pp L831-834	
		"Growth Morphology and the Equilibrium Shape: The Role of "Surfactants" in Ge/Si Island Foundation", D. Eaglesham, et al., Physical Review Letters, Vol. 70, No. 7, pgs 996-968	
		"Reduction mechanisms for defect densities in GaN using one-or two-step epitaxial lateral overgrowth methods", P. Vennegues, et al., Journal of Applied Physics, vol. 87, no. 9	
		"The effect of H2 on morphology evolution during GaN metalorganic chemical vapor deposition", J. Han, et al., Appl. Phys. Lett. 71, 24 Nov. 1997, pgs 3114-3116	
		"Optimization of Si/N Treatment Time of Sapphire Surface and Its Effect on the MOVPE GaN Overlayers", S. Haffouz, et al., pgs 677-681	
		"Oscillator strengths for optical band-to-band processes in GaN epilayers", B. Gil, Physical Review B, vol, 54, No. 11, 1996 The American Physical Society, pgs 7678-7681	
		"High-Resolution Photoluminescence and Reflectance Spectra of Homeopitaxial GaN Layers", K. Kornitzer, et al., pg 5-9	
		"Dynamics of excitonic recombination and interactions in homoepitaxial GaN", K Korona, 2002 the American Physical Society, 8 pages	

Examiner	Date	
Signature	Considered	

Based on PTO/SB/08B (08-03) as modified by Blakely, Solokoff, Taylor & Zafman (wir) 08/11/2003. Send To: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

^{*}Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

¹Applicant's unique citation designation number. ²Applicant is to place a check mark here if English language Translation is attached.

~ ·	OB 12/2					
DEC 247	Substitute	for form 1449A/PTO				Complete if Known
	\$4-0			OUDE	Application Number	10/695,724
A True a S	SUBSTITUTE FOR FORMATION DISCLOSURE			JSURE	Filing Date	October 28, 2003
SENI B	STAT	EMENT BY AP	PΙ	ICANT	First Named Inventor	Eric Frayssinet
	01711	(use as many sheets as ne			Art Unit	
		luse as many sheets as he	T	ar y,	Examiner Name	Rori Burch
	Sheet		of		Attorney Docket Number	15675P314CX

	U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.1	Document Number Number - Kind Code ² (if known)	Publication Date or Issue Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
		US-6475882	11-05-2002	Sakai et al.			
		US-	-				
		US-					
		US-					
		US-					
		US-					
		US-					
		US-					
		US-					
		US-			,		
		US-					
		US-					
		US-					
		US-					
		US-					
		US-					
		US-					
		US-					
		US-					
		US-					

	FOREIGN PATENT DOCUMENTS									
Examiner	Cite	te Foreign Patent Document Publicatio					Pages, Columns, Lines.	75		
Initials*	No.¹	Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	10				
		0506146 A2	04-06-1981	Massachusetts Institute of Technology						
	<u></u>	PCT/FR 03/02340	07-24-2003							
	<u></u>									

Examiner Signature	Date Considered	

Based on PTO/SB/08A (08-03) as modified by Blakely, Solokoff, Taylor & Zafman (wlr) 08/11/2003.

^{*}Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.